

Features

- High Accuracy

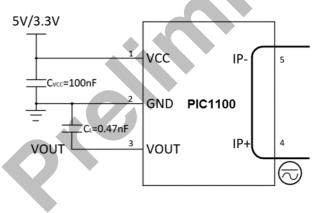
 Large Current
 - 0~200A Current Sensor
 - Offset temperature drift: ±5mV
 - Sensitivity total output error:±1%
 - Typical sensitivity temperature drift: ±0.2%
 - Typical linearity error: ±0.2%High
- Bandwidth
 Fast Response
 - Typical Bandwidth: 250kHz
 - Typical response time: 1.5µs
- High Anti-interference

 High Isolation
 - The integrated magnetic core resists stray magnetic field interference.
 - High Isolated Voltage : 5kVrms.

Package



Application Circuits



Typical Application Circuit Diagram

Description

The PIC1100 series is an open-loop Hall current sensing chip that combines high accuracy, high bandwidth, high response, high linearity, and low temperature drift. PIC1100 provides 0~200A large current measurement range. PIC1100 can also do -40 $^{\circ}$ ~ 125 $^{\circ}$ full temperature range of typical sensitivity temperature drift ± 0.2% of the performance indicators. It provides a new solution for the high accuracy and high performance current sensor area. PIC1100 adapts to strong electromagnetic and high isolation current detection environment. In addition, PIC1100 series products have passed CE, TUV and other certifications.

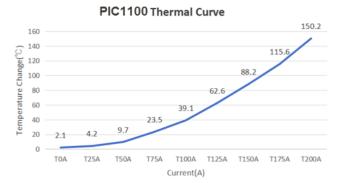




Applications

- Photovoltaic Inverter
- Industrial Inverter
- Commercial Air Conditioning
- Charging Station
- Welding Machine
- Balancing Car
- UPS

Thermal Curve



Thermal Curve is measured with the room temperature and no wind. The thermal response is highly depends on PCB layout, cooling techniques, copper thickness.

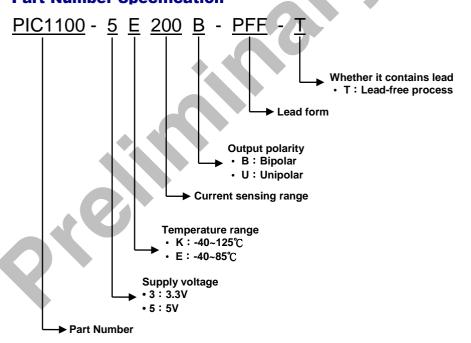


Selection Guide

Part Number	Output Mode	IPR(A)	Sensitiv	ity(mV/A)	Lead Form	Operating	Packing	
Part Number	Output Mode	IPK(A)	*=3	*=5	Lead Form	Temperature	racking	
PIC1100-*K050U-PFF-T					PFF			
PIC1100-*K050U-PSS-T		50	52.8	80	PSS			
PIC1100-*K050U-SMT-T					SMT			
PIC1100-*K050B-PFF-T					PFF			
PIC1100-*K050B-PSS-T		±50	26.4	40	PSS			
PIC1100-*K050B-SMT-T					SMT			
PIC1100-*K100U-PFF-T					PFF			
PIC1100-*K100U-PSS-T		100	26.4	40	PSS			
PIC1100-*K100U-SMT-T					SMT	-40°C ~ 125°C		
PIC1100-*K100B-PFF-T					PFF	-40 C ** 123 C		
PIC1100-*K100B-PSS-T		±100	13.2	20	PSS			
PIC1100-*K100B-SMT-T	Ratiometric				SMT		40 pieces	
PIC1100-*K150U-PFF-T	Output Mode				PFF		per tube	
PIC1100-*K150U-PSS-T		150	17.6	26.66	PSS			
PIC1100-*K150U-SMT-T					SMT			
PIC1100-*K150B-PFF-T					PFF			
PIC1100-*K150B-PSS-T		±150	8.8	13.33	PSS			
PIC1100-*K150B-SMT-T					SMT			
PIC1100-*E200U-PFF-T					PFF			
PIC1100-*E200U-PSS-T		200	13.2	20	PSS			
PIC1100-*E200U-SMT-T	1				SMT	10%		
PIC1100-*E200B-PFF-T	1				PFF	-40°C ~ 85°C		
PIC1100-*E200B-PSS-T	1	±200	6.6	10	PSS			
PIC1100-*E200B-SMT-T					SMT			

Note: Changes in ambient temperature may affect the maximum operating current of the product. For specific information, please refer to the derating curve. If you have other range requirements, please contact our sales. New range will be added without notice.

Part Number Specification





Absolute Maximum Rating

Characteristic	Symbol	Unit	Test Conditions	Min.	Тур.	Max.
Supply Voltage	Vcc	V	T _A =25°C	-0.3		6.5
Output Current	IOUTmax	mA	T _A =25°C	-45		45
Proportional output	Voutmax	V	T _A =25°C	0.1		Vcc - 0.1
Storage temperature	Ts	°C		-55		150
Operating Ambient Temperature	T _A	°C		-40		125
Maximum Junction Temperature	TJmax	°C				165

Note: Operation outside the absolute maximum ratings may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under recommended operating conditions. If used outside the recommended operating conditions but within the absolute maximum ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shortenthe device lifetime

ESD Characteristics

Characteristic	Symbol	Unit	Test Conditions	Value
Human Body Model	V _{HBM}	kV		±6
Charged Device Model	Vcdm	kV	ESD between any two pins	±1

Isolation Characteristics

Characteristic	Symbol	Unit	Test Conditions	Value
Dielectric Surge Voltage	Vsurge	V	Test method refers to IEC61000-4-5, 1.2µs/50µs waveform.	8000
Dielectric Strength Test Voltage	Viso	Valla	60s, 50Hz isolation withstand voltage parameters, according to UL62368-1, test 6kV/1s before delivery to verify the insulation performance, and verify the partial discharge is less than 5pc.	
Working Voltage for Basic	N	VPK or Vcc	Maximum approved working voltage for basic (single) isolation according to UL 60950-1	1800
Isolation	Vwvbi	Vrms	(edition 2).	1272
Working Voltage for	Vwvri	V _{PK} or V _{CC}	Maximum approved working voltage for reinforced	900
Reinforced Isolation	VWVRI	V _{RMS}	isolationaccording to UL 60950-1 (edition 2).	636

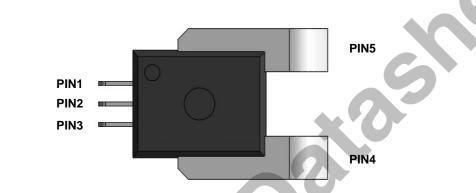
Typical Overcurrent Capability

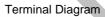
Characteristic	Symbol	Unit	Test Conditions	Value
			T₄=25°C, Current On 1s, off 99s, Apply 100 pulses	1200
Maximum Current Test	IPOC	А	T _A =85°C, Current On 1s, off 99s, Apply 100 pulses	900
			T _A =125°C, Current On 1s, off 99s, Apply 100 pulses	600

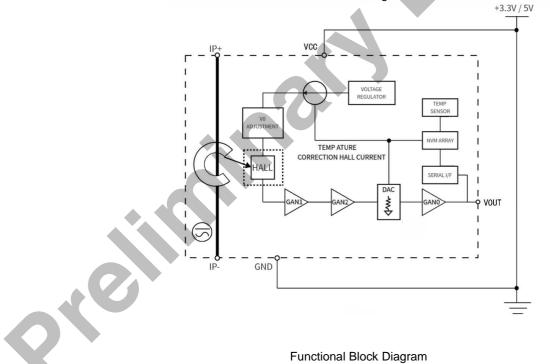


Terminal list & Functional Block

Number Name		Description
1	VCC Device power supply terminal	
2	GND ground terminal	
3	VOUT	Analog output signal
4	IP+	Current flows into the chip, positive direction
5	IP-	Current flows out of the chip, negative direction







Ver.0.01



Electrical Characteristics

Unless otherwise specified, refers to general test conditions: $T_A=25^{\circ}C + V_{CC}=5V/3.3V + C_L=0.47nF + C_{VCC}=100nF$

Characteristic	Symbol	Unit	Test Conditions	Min.	Тур.	Max.
			PIC1100-*K050U-XXX-T	0		50
			PIC1100-*K050B-XXX-T	-50		50
			PIC1100-*K100U-XXX-T	0		100
Deted Current		•	PIC1100-*K100B-XXX-T	-100		100
Rated Current	I _{PN}	A	PIC1100-*K150U-XXX-T	0		150
			PIC1100-*K150B-XXX-T	-150		150
			PIC1100-*E200U-XXX-T	0	_	200
			PIC1100-*E200B-XXX-T	-200		200
Cumple Vallage	14	V	*=3	3	3.3	3.6
Supply Voltage	Vcc	V	*=5	4.5	5	5.5
Currente a Currence ANdrie 1			*=3	6	6.5	12
Supply Current ^{Note1}	I _{CC}	mA	*=5	6	7.5	12
Primary Conductor Resistance ^{Note1}	R _P	mΩ		-	0.1	
Power-On Time ^{Note2}	T _{PO}	ms	Chip power-on ($V_{\text{CC}}\!\!>\!\!3.0\text{V}$) , V_{OUT} stable time		1	
Rise time	T _R	μs			1	
Propagation Delay	T _{PROP}	μs			0.5	
Response Time	TRESPONSE	μs			1.5	
Output Capacitive Load ^{Note2}	CL	nF	Vout - VGND		0.47	10
Output Resistive Load ^{Note2}	R∟	kΩ		4.7		
DC Output Resistance ^{Note2}	Rout	Ω			1	
Line dama alterna i se si se si Note1	V _{UVLOD}	V	Undervoltage protection rising threshold		2.3	
Undervoltage-Lockout ^{Note1}	V _{UVLOE}	V	Undervoltage protection drop threshold		2.1	
Line dama a la sur la sur sul Note1	TUVLOD	μs	Undervoltage protection rise time		500	
Undervoltage-Lockout ^{Note1}	TUVLOE	μs	Undervoltage protection drop time		50	
Outrout Current Conchility	I _{SINK}	mA	Sink current of output Pin		50	
Output Current Capability	ISOURCE	mA	Source current of output Pin		55	
Output Voltage Range	Vs	V	RL=10k Ω to V $_{\rm CC}$ or GND	0.1		V _{cc} -0.1
Internal Bandwidth	BW	kHz	200A range, small signal measurement		250	
Sensitivity Symmetry Error	ESYM	%		-0.1	±0.01	0.1
Ratiometric Output Sensitivity Error ^{Note1}	e.	0/	V _{cc} =3.15~3.45V	-0.5	0	0.5
Error ^{Note1}	S _{ERR}	%	V _{cc} =4.75~5.25V	-0.5	0	0.5
Nonlinearity ^{Note1}	_	%	<=100A	-0.1	0.03	0.1
INUT III leafily	ELIN	70	<=200A	-0.2	0.05	0.2
			T _A =85°C ~ 125°C	-1.0	±0.2	1.0
ensitivity Temperature Drift Note1	dS _{ERR}	%	T _A =25°C ~ 85°C	-0.8	±0.2	0.8
			T _A =-40°C ~ 25°C	-1.0	±0.2	1.0
			T _A =25°C ~ 125°C	-5		5
Offset Temperature Drift ^{Note1}	VIOUT(Q)TC	mV	T _A =-40°C ~ 25°C	-5		5

Note2: These parameters are guaranted by design.



PIC1100-*K050U-XXX-T/PIC1100-*K050B-XXX-T Performance Characteristic

Unless otherwise specified, refers to general test conditions: $T_A=25^{\circ}C + V_{CC}=5V/3.3V + C_L=0.47nF + C_{Vcc}=100nF$

Characteristic	Symbol	Unit	Test Conditions	Min.	Тур.	Max.	
Nominal Performance	e						
	Sens	mV/A	I _{PRmin} < I _{PR} < I _{Prmax} PIC1100-3K050U-XXX-T		Vcc*52.8 /3.3	-	
Sensitivity(Vcc=3.3V)	Sens	mv/A	I _{PRmin} < I _{PR} < I _{Prmax} PIC1100-3K050B-XXX-T		Vcc*26.4 /3.3	~~~	
Sopoitivity $(1/25)/1$	Sens	mV/A	I _{PRmin} < I _{PR} < I _{Prmax} PIC1100-5K050U-XXX-T		Vcc*80/5		
Sensitivity(V _{CC} =5V)	Sens	mv/A	I _{PRmin} < I _{PR} < I _{Prmax} PIC1100-5K050B-XXX-T	~	Vcc*40/5		
Zero Current Output		V	Unipolar, I _{PR} =0A		Vcc*0.1		
Voltage			Bipolar, I _{PR} =0A		Vcc*0.5		
Accuracy Performan	ce						
Noise	VN	mVrms			7		
		I	mV	I _P =0A · I _{PRmax}		0.4	
Magnetic Offset Error	I _{ERROM}	mA	I _P =0A · I _{PRmax}		10		
Total Output Error	Етот	%	Ip=Ip _{Rmax} · T _A =-40°C ∼ 125°C	-1	±0.2	1	
Total Output Error C	omponents	: Е _{тот} = (Vı	OUT -VIOUTIdeal) / (Sensideal × IP) × 100%				
Sensitivity Error	Esens	%	IP=IPRmax · TA=25℃ ~ 125℃	-0.5	±0.2	0.5	
			I _P =0A · T _A =25°C ~ 125°C	-10	±0.2	10	
Voltage Offset Error	V _{OE}	mV	IP=0A · T _A =25℃	-5	±0.2	5	
			I₽=0A · T _A =-40°C ~ 125°C	-10	±0.2	10	
Lifetime Drift Charac	teristics						
Sensitivity Error Lifetime Drift	Esens_drift	%	After reliability test · T _A =25°C		±0.5		
Total Output Error Lifetime Drift	ETOT_drift	%	After reliability test · T _A =25°C		±0.5		

Note : The data is obtained from laboratory testing with 3 σ data



PIC1100-*K100U-XXX-T/PIC1100-*K100B-XXX-T Performance Characteristic

Unless otherwise specified, refers to general test conditions: $T_A=25^{\circ}\text{C} + V_{CC}=5\text{V}/3.3\text{V} + \text{C}_{L}=0.47\text{nF} + \text{C}_{Vcc}=100\text{nF}$

Characteristic	Symbol	Unit	Test Conditions	Min.	Тур.	Max.					
Nominal Performanc	e										
Constitute () (c 2.2) ()	Sens	mV/A	I _{PRmin} < I _{PR} < I _{Prmax} PIC1100-3K100U-XXX-T		Vcc*26.4 /3.3	-					
Sensitivity(Vcc=3.3V)	Sens	mv/A	I _{PRmin} < I _{PR} < I _{Prmax} PIC1100-3K100B-XXX-T		Vcc*13.2 /3.3	~~~					
Soncitivity $(1/a - 5)/1$	Sens	mV/A	I _{PRmin} < I _{PR} < I _{Prmax} PIC1100-5K100U-XXX-T		Vcc*40/5						
Sensitivity(V _{CC} =5V)	Sens	IIIV/A	I _{PRmin} < I _{PR} < I _{Prmax} PIC1100-5K100B-XXX-T	-	Vcc*20/5						
Zero Current Output	Violitio	V	Unipolar, I _{PR} =0A		V _{cc} *0.1						
Voltage	V 100 I (Q)	VIOUT(Q)	V IOUT(Q)	VIOUI(Q)	V 100 I (Q)	V 100 I (Q)	v	Bipolar, I _{PR} =0A		Vcc*0.5	
Accuracy Performan	се										
Noise	V _N	mVrms			5						
		mV	I _P =0A · I _{PRmax}		0.6						
Magnetic Offset Error	I _{ERROM}	mA	I _P =0A · I _{PRmax}		30						
Total Output Error	Етот	%	IP=IPRmax · TA=-40°C ~ 125°C	-1	±0.2	1					
Total Output Error C	omponents	: Етот = (V	DUT -VIOUTIdeal) / (Sensideal × IP) × 100%		· · · · ·						
Sensitivity Error	Esens	%	I₽=I₽Rmax · TA=25°C ~ 125°C	-0.5	±0.2	0.5					
			I _P =0A · T _A =25°C ~ 125°C	-10	±0.2	10					
Voltage Offset Error	V _{OE}	mV	I₽=0A · TA=25°C	-5	±0.2	5					
			Ip=0A · T _A =-40°C ~ 125°C	-10	±0.2	10					
Lifetime Drift Charac	teristics										
Sensitivity Error Lifetime Drift	E _{SENS_drift}	%	After reliability test · T _A =25°C		±0.5						
Total Output Error Lifetime Drift	ETOT_drift	%	After reliability test · T _A =25°C		±0.5						

Note : The data is obtained from laboratory testing with 3 σ data



PIC1100-*K150U-XXX-T/PIC1100-*K150B-XXX-T Performance Characteristic

Unless otherwise specified, refers to general test conditions: $T_A=25^{\circ}\text{C} + V_{CC}=5\text{V}/3.3\text{V} + \text{C}_{L}=0.47\text{nF} + \text{C}_{Vcc}=100\text{nF}$

Characteristic	Symbol	Unit	Test Conditions	Min.	Тур.	Max.
Nominal Performance	e				11	
Sensitivity(Vcc=3.3V)			I _{PRmin} < I _{PR} < I _{Prmax} PIC1100-3K150U-XXX-T		Vcc*17.6 /5	
Sensitivity(Vcc=3.3V)	Sens	mV/A	I _{PRmin} < I _{PR} < I _{Prmax} PIC1100-3K150B-XXX-T		Vcc*8.8 /5	
Sensitivity(V _{CC} =5V)	Sens	mV/A	I _{PRmin} < I _{PR} < I _{Prmax} PIC1100-5K150U-XXX-T		V _{CC} *26.66 /5	
Sensitivity(VCC=SV)	06115	IIIV/A	I _{PRmin} < I _{PR} < I _{Prmax} PIC1100-5K150B-XXX-T	-	Vcc*13.33 /5	
Zero Current Output	Manaka	V	Unipolar, I _{PR} =0A		Vcc*0.1	
Voltage	VIOUT(Q)	v	Bipolar, I _{PR} =0A		V _{cc} *0.5	
Accuracy Performan	ce					
Noise	VN	mVrms			4	
Magnatia Offact Error	ERROM	mV	I _P =0A · I _{PRmax}		0.8	
Magnetic Offset Error	IERROM	mA	I _P =0A · I _{PRmax}		60	
Total Output Error	Етот	%	I _P =I _{PRmax} · T _A =-40°C ∼ 125°C	-1	±0.2	1
Total Output Error C	omponents	: Етот = (V	OUT -VIOUTIdeal) / (Sensideal × IP) × 100%			
Sensitivity Error	Esens	%	IP=IPRmax · TA=25°C ∼ 125°C	-0.5	±0.2	0.5
			I₽=0A · TA=25°C ~ 125°C	-10	±0.2	10
Voltage Offset Error	V _{OE}	mV	I₽=0A · TA=25°C	-5	±0.2	5
			I₽=0A · TA=-40°C ~ 125°C	-10	±0.2	10
Lifetime Drift Charac	teristics					
Sensitivity Error Lifetime Drift	Esens_drift	%	After reliability test · T _A =25°C		±0.5	
Total Output Error Lifetime Drift	E _{TOT_drift}	%	After reliability test · T _A =25°C		±0.5	

Note : The data is obtained from laboratory testing with 3 σ data



PIC1100-*E200U-XXX-T/PIC1100-*E200B-XXX-T Performance Characteristic

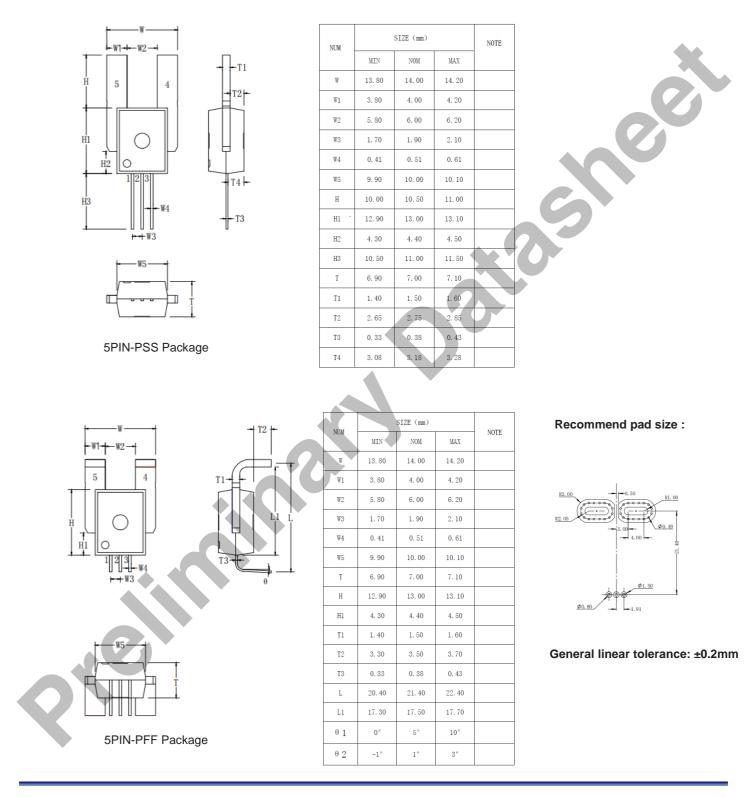
Unless otherwise specified, refers to general test conditions: $T_A=25^{\circ}C + V_{CC}=5V/3.3V + C_L=0.47nF + C_{Vcc}=100nF$

Characteristic	Symbol	Unit	Test Conditions	Min.	Тур.	Max.
Nominal Performanc	e			1	11	
Constitute () (Sens	mV/A	I _{PRmin} < I _{PR} < I _{Prmax} PIC1100-3E200U-XXX-T		Vcc*13.2 /3.3	-
Sensitivity(Vcc=3.3V)	Sens	IIIV/A	I _{PRmin} < I _{PR} < I _{Prmax} PIC1100-3E200B-XXX-T		Vcc*6.6 /3.3	~~
Soncitivity $(1/a - 5)/1$	Sens	mV/A	I _{PRmin} < I _{PR} < I _{Prmax} PIC1100-5E200U-XXX-T		Vcc*20/5	
Sensitivity(V _{CC} =5V)	Sens	IIIV/A	I _{PRmin} < I _{PR} < I _{Prmax} PIC1100-5E200B-XXX-T	~	Vcc*10/5	
Zero Current Output	Viout(q)	V	Unipolar, I _{PR} =0A		V _{cc} *0.1	
Voltage	V 100 I (Q)	v	Bipolar, I _{PR} =0A		Vcc*0.5	
Accuracy Performan	се					
Noise	VN	mVrms			3	
	1	mV	I _P =0A · I _{PRmax})	1	
Magnetic Offset Error	I _{ERROM}	mA	I _P =0A · I _{PRmax}		100	
Total Output Error	Етот	%	IP=IPRmax · TA=-40°C ~ 125℃	-1	±0.2	1
Total Output Error C	omponents	: Е _{тот} = (V	OUT -VIOUTIdeal) / (Sensideal × IP) × 100%			
Sensitivity Error	Esens	%	Ip=IpRmax · TA=25℃ ~ 125℃	-0.5	±0.2	0.5
			I _P =0A · T _A =25°C ~ 125°C	-10	±0.2	10
Voltage Offset Error	V _{OE}	mV	I₽=0A · TA=25°C	-5	±0.2	5
			I⊵=0A · T _A =-40°C ~ 125°C	-10	±0.2	10
Lifetime Drift Charac	teristics					
Sensitivity Error Lifetime Drift	E _{SENS_drift}	%	After reliability test · T _A =25°C		±0.5	
Total Output Error Lifetime Drift	ETOT_drift	%	After reliability test · T _A =25°C		±0.5	

Note : The data is obtained from laboratory testing with 3 σ data



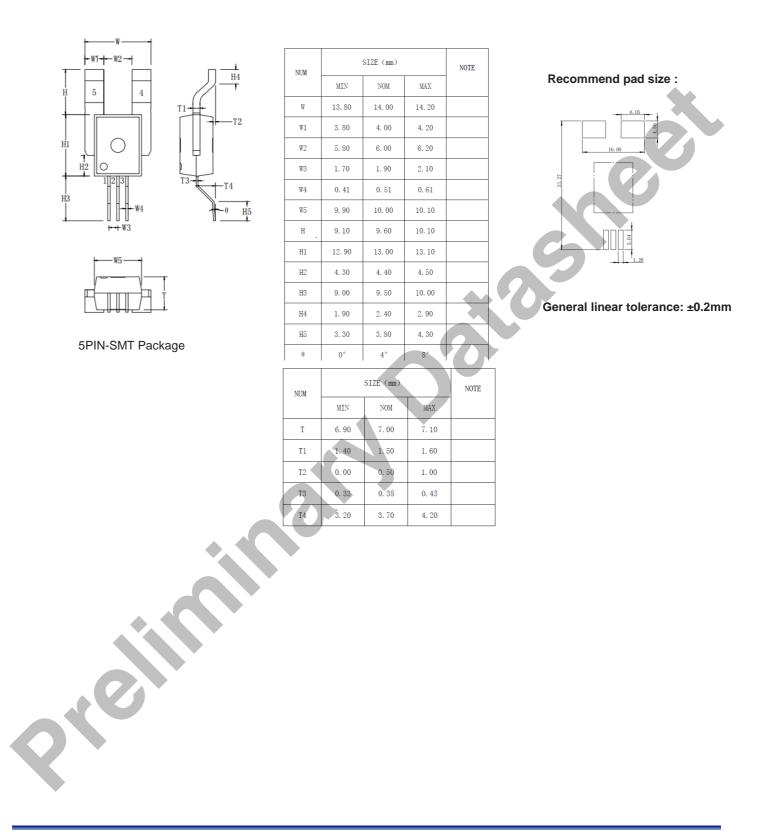
PACKAGE INFORMATION



Potens semiconductor corp.

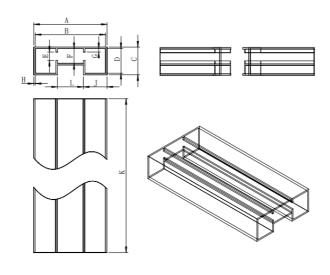
Ver.0.01







PACKING INFORMATION



NUDA				
NUM	MIN	NOM	MAX	
А	37.80	38.00	38. 20	
В	36.20	36.40	36. 60	
С	13.80	14.00	14. 20	
D	12.20	12.40	12.60	
Е	4.10	4.30	4. 50	
F	7.50	7. 70	7.90	
G	1.60	1.80	2.00	
Н	0.60	0.80	1.00	
L	13. 50	13. 70	13.90	
J	11.95	12.15	12.35	
K	589.00	590.00	591.00	

*40 pieces per tube



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